Nch 100V 20A Power MOSFET

V <sub>DSS</sub>	100V
R <sub>DS(on)</sub> (Max.)	46mΩ
I <sub>D</sub>	±20A
P <sub>D</sub>	20W

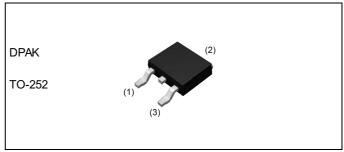
Features

- 1) Low on resistance
- 2) Fast switching speed
- 3) Drive circuits can be simple
- 4) Parallel use is easy
- 5) Pb-free lead plating; RoHS compliant
- 6) AEC-Q101 Qualified

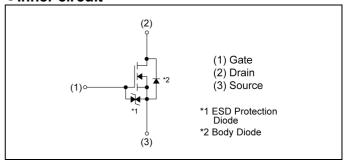
# Application

Switching

### Outline



## •Inner circuit



Packaging specifications

- : uoitugiiig opoomeuuoiio							
	Packing	Embossed Tape					
	Reel size (mm)	330					
Туре	Tape width (mm)	16					
	Quantity (pcs)	2500					
	Taping code	TL					
	Marking	RD3P200SN					

# ● **Absolute maximum ratings** (T<sub>a</sub> = 25°C ,unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V <sub>DSS</sub>	100	V
Continuous drain current	I <sub>D</sub> *1	±20	Α
Pulsed drain current	I <sub>DP</sub> *2	±80	Α
Gate - Source voltage	V <sub>GSS</sub>	±20	V
Avalanche current, single pulse	I <sub>AS</sub> *3	10	Α
Avalanche energy, single pulse	E <sub>AS</sub> *3	72	mJ
Power dissipation	P <sub>D</sub> *4	20	W
Junction temperature	T <sub>j</sub>	150	°C
Operating junction and storage temperature range	T <sub>stg</sub>	-55 to +150	°C

# ●Thermal resistance

Parameter	Cymph ol	Values			l leit
Parameter	Symbol	Min.	Тур.	Max.	Unit
Thermal resistance, junction - case	R <sub>thJC</sub> *4	-	1	6.25	°C/W

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

Davanastan	Symbol Conditions -		Values			1.1
Parameter			Min.	Тур.	Max.	Unit
Drain - Source breakdown voltage	V <sub>(BR)DSS</sub>	$V_{(BR)DSS}$ $V_{GS} = 0V, I_D = 1mA$		-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_{j}}$	I <sub>D</sub> = 1mA referenced to 25°C	1	116.9	1	mV/°C
Zero gate voltage drain current		V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V	-	-	1	μA
Gate - Source leakage current I <sub>GSS</sub>		$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±10	μΑ
Gate threshold voltage	$V_{GS(th)}$	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	1.0	-	2.5	V
Gate threshold voltage temperature coefficient	$\frac{\DeltaV_{GS(th)}}{\DeltaT_j}$	I <sub>D</sub> = 1mA referenced to 25°C	-	-3.6	-	mV/°C
Static drain - source	D *5	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A	-	33	46	0
on - state resistance	R <sub>DS(on)</sub> *5	V <sub>GS</sub> = 4.0V, I <sub>D</sub> = 20A	-	36 50		mΩ
Gate resistance	$R_{G}$	f = 1MHz, open drain	-	4.9	-	Ω
Forward Transfer Admittance	Y <sub>fs</sub>  *5	V <sub>DS</sub> = 10V, I <sub>D</sub> = 20A	15	-	-	S

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

Darameter	Cumbal	Conditions	Values			Unit	
Parameter	Symbol Conditions —		Min.	Тур.	Max.	Offic	
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	2100	-		
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 25V	-	180	-	pF	
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	120	1		
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \simeq 50V, V_{GS} = 10V$	•	100	ı		
Rise time	<b>t</b> <sub>r</sub> *5	I <sub>D</sub> = 10A	•	35	ı	no	
Turn - off delay time	t <sub>d(off)</sub> *5	$R_L \simeq 5\Omega$	-	150	-	ns	
Fall time	<b>t</b> <sub>f</sub> *5	$R_G = 10\Omega$	-	100	-		

# ● Gate charge characteristics (T<sub>a</sub> = 25°C)

Doromotor	Cumbal	Conditions	Values			Lloit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Total gate charge	$Q_g^{*5}$	V <sub>DD</sub> ≃ 50V,	-	55	-	
Gate - Source charge	Q <sub>gs</sub> *5	I <sub>D</sub> = 20A,	-	5.5	-	nC
Gate - Drain charge	Q <sub>gd</sub> *5	V <sub>GS</sub> = 10V	-	12.5	-	

# ● Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Darameter	Cumbal	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Continuous forward current	Is*1	T = 25°0	-	-	14	Α
Pulse forward current	I <sub>SP</sub> *2	T <sub>a</sub> = 25°C	-	-	80	Α
Forward voltage	V <sub>SD</sub> *5	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A	-	-	1.5	V
Reverse recovery time	t <sub>rr</sub> *5	I <sub>S</sub> = 10A, V <sub>GS</sub> =0V	-	53	-	ns
Reverse recovery charge	Q <sub>rr</sub> *5	di/dt = 100A/µs	ı	120	ı	μC

<sup>\*1</sup> Limited only by maximum temperature allowed.

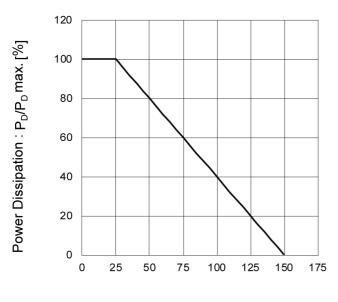
<sup>\*2</sup> Pw≦10µs , Duty cycle≦1%

<sup>\*3</sup> L  $\simeq$  1mH, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 $\Omega$ , Starting T<sub>j</sub> = 25 $^{\circ}$ C Fig.3-1,3-2

<sup>\*4</sup> T<sub>c</sub>=25°C

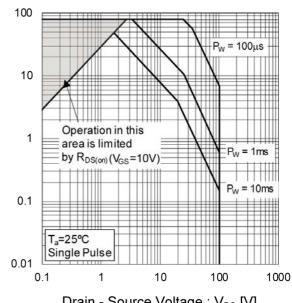
<sup>\*5</sup> Pulsed

Fig.1 Power Dissipation Derating Curve



Junction Temperature : T<sub>i</sub> [°C]

Fig.2 Maximum Safe Operating Area



Drain Current : I<sub>D</sub> [A]

Drain - Source Voltage: V<sub>DS</sub> [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

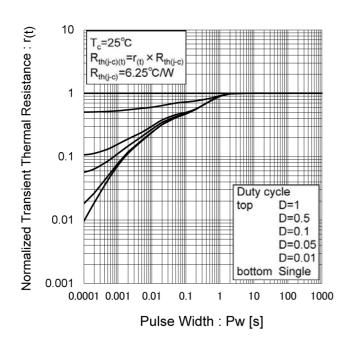


Fig.4 Single Pulse Maximum Power dissipation

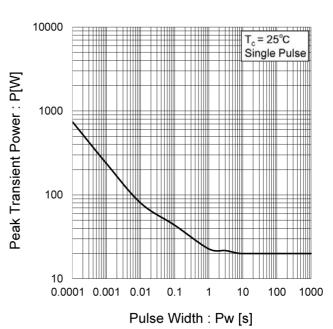


Fig.5 Typical Output Characteristics(I)

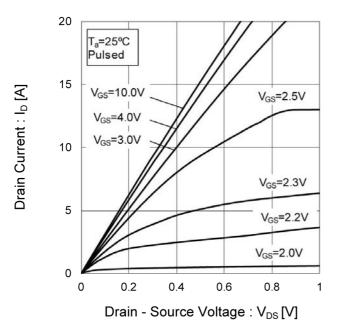
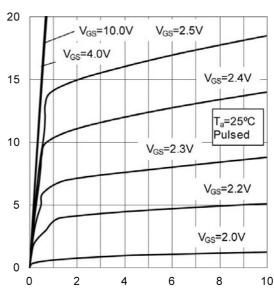


Fig.6 Typical Output Characteristics(II)



Drain Current : I<sub>D</sub> [A]

Drain - Source Voltage: V<sub>DS</sub> [V]

Fig.7 Breakdown Voltage vs.
Junction Temperature

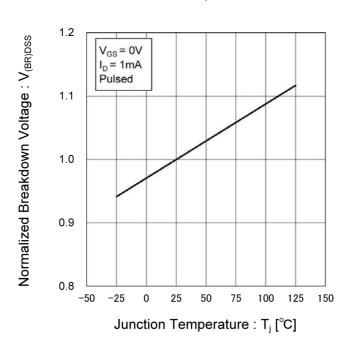


Fig.8 Typical Transfer Characteristics

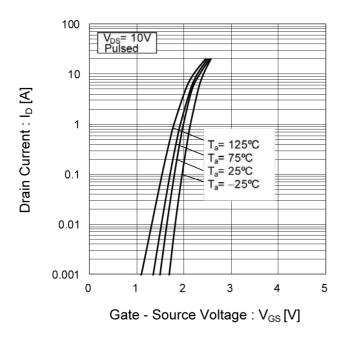
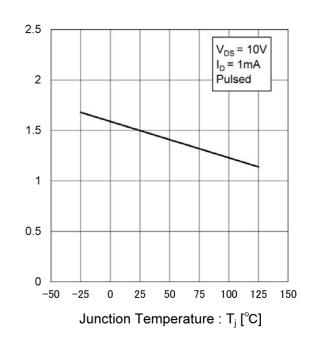


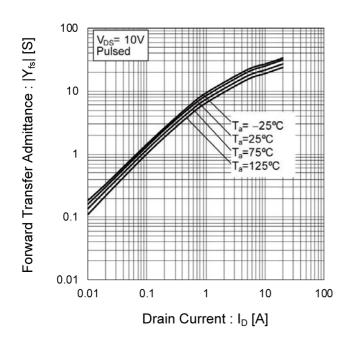
Fig.9 Gate Threshold Voltage vs. Junction Temperature



Gate Threshold Voltage: VGS(th) [V]

6/11

Fig.10 Forward Transfer Admittance vs. **Drain Current** 



RD3P200SNFRA Datasheet

# • Electrical characteristic curves

Fig.11 Drain Current Derating Curve

120 100 Drain Current Dissipation 80 : I<sub>D</sub>/I<sub>D</sub>max. [%] 60 40 20 0 0 -25 25 50 75 100 125 150 Junction Temperature : T<sub>j</sub> [°C]

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

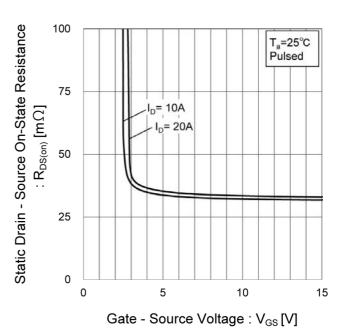


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

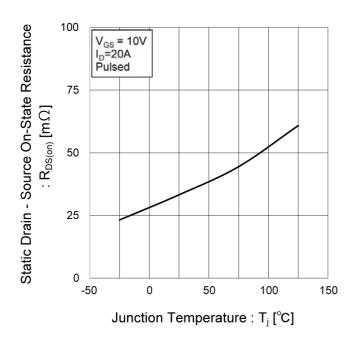


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

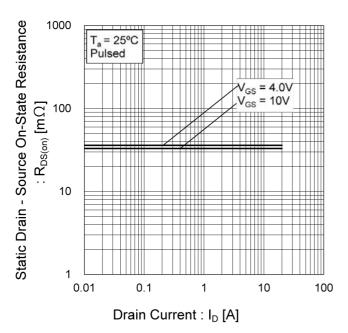


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

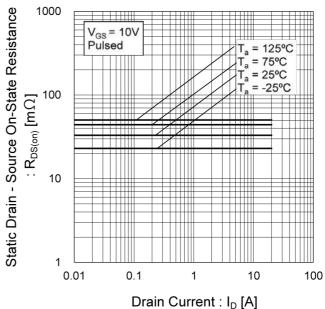


Fig.16 Static Drain - Source On - State
Resistance vs. Drain Current(III)

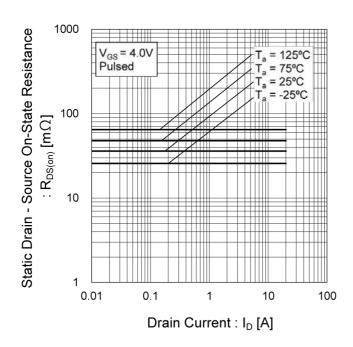


Fig.17 Typical Capacitance vs.

Drain - Source Voltage

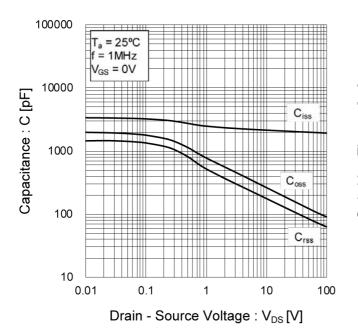


Fig.18 Switching Characteristics

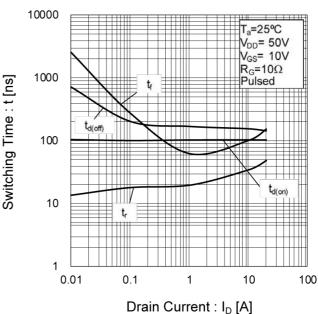


Fig.19 Dynamic Input Characteristics

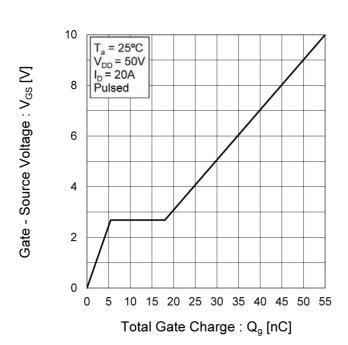
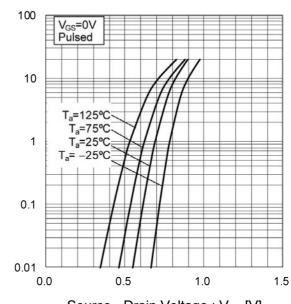


Fig.20 Source Current vs.

Source Drain Voltage



Source Current : I<sub>s</sub> [A]

# Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

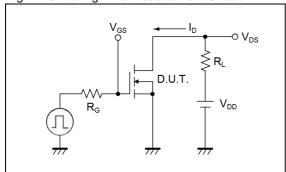


Fig.2-1 Gate Charge Measurement Circuit

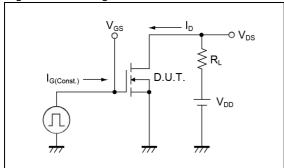


Fig.3-1 Avalanche Measurement Circuit

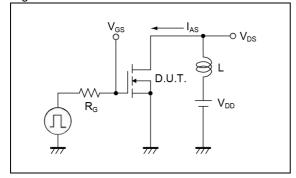


Fig.1-2 Switching Waveforms

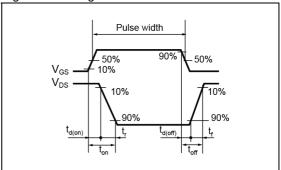


Fig.2-2 Gate Charge Waveform

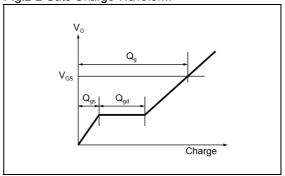
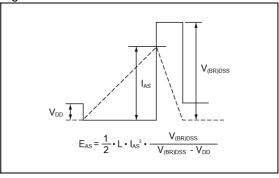
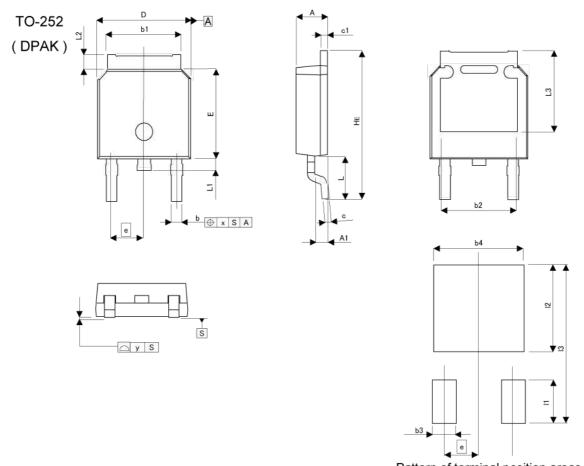


Fig.3-2 Avalanche Waveform



# Dimensions



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM -	MILIME	ETERS	INC	HES	
DIIVI	MIN	MAX	MIN	MAX	
Α	2.10	2.30	0.083	0.091	
A1	0.70	1.10	0.028	0.043	
b	0.65	0.85	0.026	0.033	
b1	5.10	5.40	0.201	0.213	
b2	5.	10	0.2	201	
С	0.40	0.60	0.016	0.024	
c1	0.40	0.60	0.016	0.024	
D	6.40	6.80	0.252	0.268	
е	2.	30	0.091		
E	6.00	6.40	0.236	0.252	
HE	9.50	10.50	0.374	0.413	
L	2.	90	0.1	14	
L1	0.70	0.90	0.028	0.035	
L2	0.70	1.30	0.028	0.051	
L3	5.30		0.209		
х	-	0.10	160	0.004	
у	-	0.10	-	0.004	

DIM	MILIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
b3	₽	1.10	623	0.043
b4	*	5.40	5,41	0.213
I1 .	<u> </u>	2.90	72	0.114
12	*	5.50	5.00	0.217
13	<u>s</u>	10.50	021	0.413

Dimension in mm/inches



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(Note1) Medical Equipment Classification of the Specific Applications

( )			
JAPAN	USA	EU	CHINA
CLASSⅢ	CLASSⅢ	CLASS II b	CLASSⅢ
CLASSIV	CLASSIII	CLASSⅢ	CLASSIII

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  - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

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- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

### **Precaution for Storage / Transportation**

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
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  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
  may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
  exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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Rev.001

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